REMARKS

The specification has been amended to provide a cross-reference to the previously filed International Application. The claims have also been amended to delete multiple dependencies and to place the application into better form for examination. Entry of the present amendment and favorable action on the above-identified application are earnestly solicited.

Attached hereto is a marked-up copy of the changes made to the application by this Amendment.

If necessary, the Commissioner is hereby authorized in this, concurrent, and future replies, to charge payment or credit any overpayment to Deposit Account No. 02-2448 for any additional fees required under 37 C.F.R. § 1.16 or under 37 C.F.R. § 1.17; particularly, extension of time fees.

Respectfully submitted,

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VERSION WITH MARKINGS SHOWING CHANGES MADE

The specification has been amended to provide cross-referencing to the International Application.

The claims have been amended as follows:

3. (Amended) A method according to claim 1 [or 2], whereby the measuring is made after processing steps, such as development, etching, blasting or high-temperature processing, following the exposure.

4. (Amended) A method according to [one of the claims 1-3] claim 1, whereby the first and the second mask are based on the same input data.

5. (Amended) A method according to [one of the claims 1-3] claim 1, whereby the first mask is a reference mask based on reference input data, whereas the second mask is based on the actual product data.

6. (Amended) A method according to [any one of the claims above] claim 1, whereby the compensation used is a statistical mean value of the compensation according to the measurement and compensation according to prior measurements.

7. (Amended) A method according to [any one of the claims above] claim 1, wherein at least one additional measurement is made during the process, whereby the compensations is a statistical mean value of compensation parts related to the

process before the first measurement, and the process between the measurements.

8. (Amended) A method according to [any one of the claims above] claim 1, whereby the thickness of the sensitive layer before the exposure on the mask blank or on the substrate is measured, whereby said measurement data are used for additional compensation.

9. (Amended) A method according to [any one of the claims above] claim 1, whereby already existing patterns on the substrate is measured prior to the exposure, whereby said measurement is used for additional compensation.

10. (Amended) A method according to [any one of the claims above] claim 1, whereby said method is performed once for each substrate batch used in said fabrication.

11. (Amended) A method according to [any one of the claims above] claim 1, whereby the measurement comprises measurement of position errors and pattern line width errors.

12. (Amended) A method according to [any one of the claims above] claim 1, whereby said compensation is performed by time offsets or room offsets in the pattern writer used for producing the second mask.

15. (Amended) A system according to claim 13 [or 14], comprising at least one additional measuring device, whereby the compensations is a statistical mean value of compensation parts related to the process before the first measurement, and the process between the measurements.

16. (Amended) A system according to [one of the claims 13-15] claim 13, whereby the first and the second mask generator (1) are the same device.

17. (Amended) A system accoding to [any one of the claims 13-16] claim 13, further comprising a second measuring device (4) for measuring the thickness of the light sensitive layer on the substrate prior to the exposure, whereby said measurement is used for additional compensation.

18. (Amended) A system according to [any one of the claims 13-17] claim 13, further comprising a third measuring device (4) for measuring of existing patterns on the substrate prior to the exposure, whereby said measurement is used for additional compensation.

19. (Amended) A system according to [any one of the claims 13-18] claim 13, whereby the first measuring device comprises means for measurement of position errors and pattern line width errors.

20. (Amended) A system according to [any one of the claims 13-19] claim 13, Whereby said mask generator comprises a pattern writer, being controllable for said compensations by means of time offsets during the writing.